

# **Session WE4C**

## **Noise Modeling**

**Chairman:**

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Recent progress in noise modeling of FET devices has focused on temperature dependence and suitability for statistical treatment. Improvements are presented in calibration methods and extraction techniques. Another important topic addressed is modeling suitable for oscillator phase noise simulation.

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**3:30 p.m.–5:00 p.m., Wednesday, May 17, 1995**  
**Room 12A,B,C**